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Nota di contenuto	Intro -- Preface -- Acknowledgments -- Contents -- About the Author -- Chapter 1: The Novel Transistor Characterization Challenge -- 1.1 Introduction: Why This Book? -- 1.2 General Measurement Conditions and Terminology -- 1.2.1 Small-Signal vs Large-Signal -- 1.2.2 Frequency-Domain vs Time-Domain -- 1.2.3 Continuous-Wave vs Transient Signals -- 1.3 Overview of the Content of the Book -- Chapter 2: High-Frequency Test Equipment, Connections, and Contact with Transistors -- 2.1 Introduction -- 2.2 Signal Detection Instruments -- 2.2.1 Spectrum Analyzer -- 2.2.2 Vector Network Analyzer -- 2.2.3 Oscilloscope -- 2.3 Stimulus Instruments -- 2.4 Transmission Lines and Interconnections -- 2.5 Cables, Connectors, and Bandwidth -- 2.6 Bias Tees and Resistor Tees -- 2.7 Transistor Probing -- 2.8 Probe Pad Design -- References -- Chapter 3: Measurement of the Frequency Response of Transistors -- 3.1 Introduction -- 3.2 Methods for Low-Current Transistors -- 3.2.1 Transistor Structures -- 3.2.2 Rectification Technique -- 3.2.3 Direct Gain Measurement Technique -- 3.3 Frequency Performance Figure-of-Merit and Linear Model -- 3.3.1 AC Linear Model of Transistors -- 3.3.2 Measuring Small-Signal Current Gain with S-Parameters -- 3.3.3 Calibration -- 3.3.4 De-Embedding Procedure -- 3.3.5 Measurement Examples -- 3.3.6 Definition of the Physical Open Structure -- 3.3.7 Other Performance Figures-of-Merit -- References -- Chapter 4: Case

Studies in the Evaluation of Novel Transistors -- 4.1 Voltage Gain of a Low-Current Transistor as a Function of Frequency -- 4.2 Vertical Gate Resistance -- 4.2.1 Detecting Gate Discontinuity Using VNA Measurements -- 4.2.2 Measuring Vertical Gate Resistance in Continuous Gate Stack -- References -- Chapter 5: Measurement of the AC Linearity of Transistors -- 5.1 Linearity Overview -- 5.2 One-Tone Non-Linearity: Gain Compression. 5.3 Two-Tone Non-Linearity: Third-Order Intercept -- References -- Chapter 6: Measurement of the Large-Signal Propagation Delay of Single Transistors -- 6.1 Single Transistor Figure-of-Merit -- 6.2 Direct Propagation Delay Measurement -- 6.3 Ring Oscillators to Measure Delay -- 6.3.1 Ring Oscillator Frequency Measurement -- 6.3.2 Ring Oscillators with Novel Transistors -- 6.4 Instability in Digital Gates -- 6.4.1 Gated Ring Oscillators and Delay Chains -- 6.4.2 Transistor Aging -- 6.4.3 Drift and Jitter -- References -- Chapter 7: Measurement of the Transient Response of Transistors -- 7.1 Transient Effects in Transistors -- 7.2 Voltage Measurement Methods -- 7.3 Fast Source and Measurement Units -- 7.4 Pulsed I-V Method -- 7.5 Pulse-Train Method -- 7.6 Fast Edge Methods -- References -- Appendix A: Measuring Transistors with Controlled Temperature -- Index.
